

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	William F. Seng, et al.)	
)	
Serial No.:	TBA)	
)	Examiner: TBD
Filed:	Filed Herewith)	
)	Art Unit: TBD
For:	LOW-TEMPERATURE, LONG TERM)	
	ANNEALING OF NICKEL CONTACTS)	
	TO LOWER INTERFACIAL)	
	RESISTANCE)	

INFORMATION DISCLOSURE STATEMENT

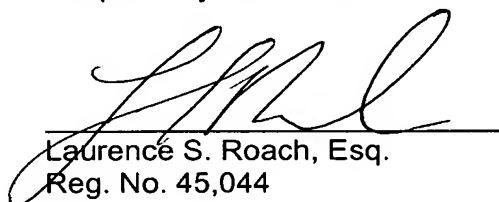
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Commissioner of Patents
P.O. Box 1450
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Dear Sir:

Pursuant to 37 CFR §1.97 - §1.98, Applicants hereby bring to the attention of the United States Patent and Trademark Office, the references listed on the attached Form PTO-1449.

Respectfully submitted,

23-MAR-2004
Date


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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	TBA
				Filing Date	Filed Herewith
				First Named Inventor	William F. Seng
				Art Unit	TBD
				Examiner Name	TBD
Sheet	1	of	1	Attorney Docket Number	90065.001090/8018.00

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	1	"Interface Chemistry and Electrical Properties of Annealed Ni and Ni/Al-6H SiC Structures", C. Halling, R. Yakimova, V. Krastev, Ts. Marinova and E. Janzen, Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.	
	2	"The Influence of Dry Cleaning Techniques on Thermal Oxides Grown on 4H and 6H P-type SiC", C.-M. Zetterling, C.I. Harris, M. Ostling and V.V. Afanas'ev", Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.	
	3	"Specific Contact Resistance as a Function of Doping N-type 4H and 6H-SiC", Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.	
	4	"Aluminum Doped 6H SiC: CVD Growth and Formation of Ohmic Contacts", Inst. Phys. Conf. Seri No. 196, 1996 IOP Publishing Ltd.	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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